

➤ General Description

This PAN75TD38CSA N-Channel enhancement mode power field effect transistor is the high density trench technology and this advanced technology can provide excellent $R_{ds(On)}$ performance and efficiency for power switching and load switching application., this device also comply with the RoHS and Green Product requirement with full function reliability approved.

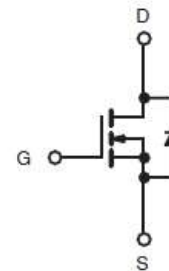
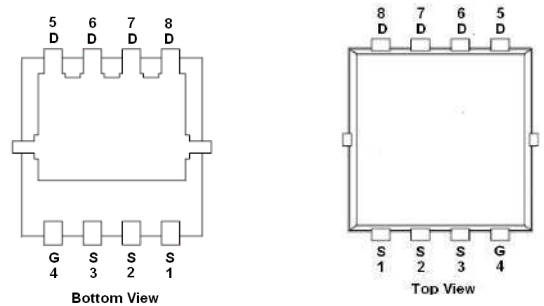
➤ Feature

- Super Low Gate Charge
- 100% EAS Guaranteed
- Green Device Available
- Excellent CdV/dt effect decline
- Advanced high cell density Trench technology
- DFN5x6B-EP1 package design

➤ Application

- DC/DC Primary Side Switch
- Industrial Synchronous
- Rectification Load Switch
- DC/DC Converters

➤ DFN3.3x3.3-8L



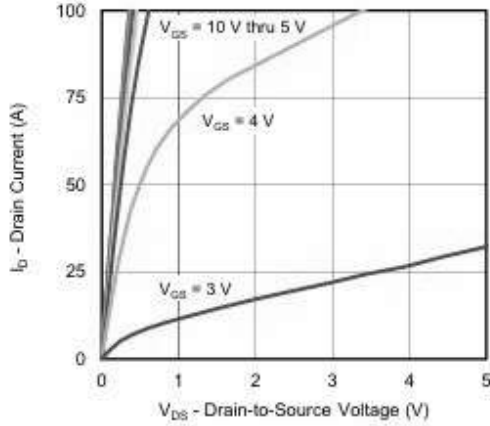
➤ Absolute Maximum Ratings

Parameter	Symbol	Typical	Unit
Drain-Source Voltage	V_{DSS}	30	V
Gate -Source Voltage	V_{GSS}	± 20	V
Continuous Drain Current($T_J=150^\circ C$)	I_{DSM}	$T_C=25^\circ C$	65
		$T_C=70^\circ C$	48
Pulsed Drain Current ($t=100\mu s$)	I_{DM}	$T_A=25^\circ C$	20
		$T_A=70^\circ C$	16
Continuous Source Current(Diode Conduction)	I_S	$T_C=25^\circ C$	200
		$T_A=25^\circ C$	32
Single Pulse Avalanche Current	I_{AS}	$L=0.1mH$	2.8
			E_{AS}
Power Dissipation	P_D	$T_C=25^\circ C$	12
		$T_C=75^\circ C$	36
Operating Junction Temperature	T_J	$T_A=25^\circ C$	22
		$T_A=75^\circ C$	3.2
Storage Temperature Range	T_{STG}	150	$^\circ C$
Thermal Resistance-Junction to Ambient	$R_{\theta JA}$	-55/150	$^\circ C$
Maximum Junction-to-Case (Drain)	$R_{\theta JC}$	$t \leq 10 s$	30
		Steady-State	2.8

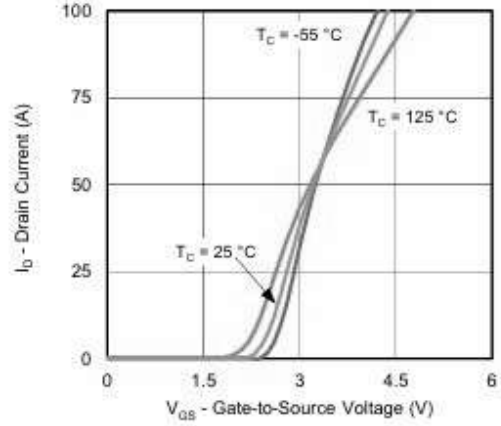
➤ Electrical Characteristics ($T_J=25^\circ C$ Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	30			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.2	1.7	2.5	
Gate Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 20V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=24V, V_{GS}=0V$			1	uA
		$V_{DS}=24V, V_{GS}=0V$ $T_J=85^\circ C$			10	
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=20A$		3.9	4.8	m Ω
		$V_{GS}=4.5V, I_D=15A$		5.8	7.2	
Forward Transconductance	g_{FS}	$V_{DS}=10V, I_D=15A$		50		S
Diode Forward Voltage	V_{SD}	$I_S=2A, V_{GS}=0V$		0.7	1.2	V
Dynamic						
Total Gate Charge	Q_g	$V_{DS}=15V, V_{GS}=10V, I_D \cong 19A$		11	18	nC
Total Gate Charge	Q_g	$V_{DS}=15V, V_{GS}=4.5V, I_D \cong 19A$		5.4		
Gate-Source Charge	Q_{gs}			2.8		
Gate-Drain Charge	Q_{gd}			1.4		
Gate Resistance	R_g	$f=1MHz$		4.1		Ω
Input Capacitance	C_{iss}	$V_{DS}=15V, V_{GS}=0V$ $f=1MHz$		790		pF
Output Capacitance	C_{oss}			390		
Reverse Transfer Capacitance	C_{rss}			38		
Turn-On Time	$t_{d(on)}$	$V_{DD}=15V, R_L=1.5\Omega$ $I_D \cong 10A, V_{GEN}=10V$ $R_G=1.0\Omega$		10	20	ns
	t_r			20	40	
Turn-Off Time	$t_{d(off)}$			20	40	
	t_f			10	20	

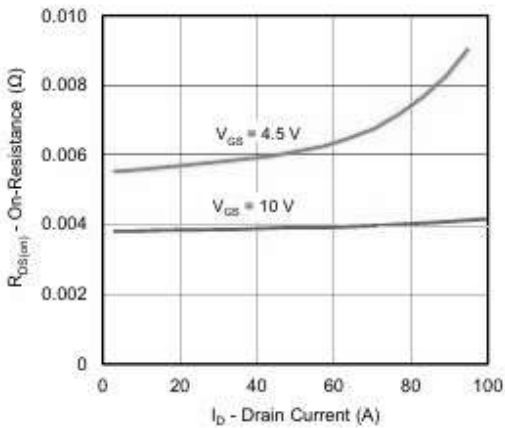
➤ Typical Characteristics



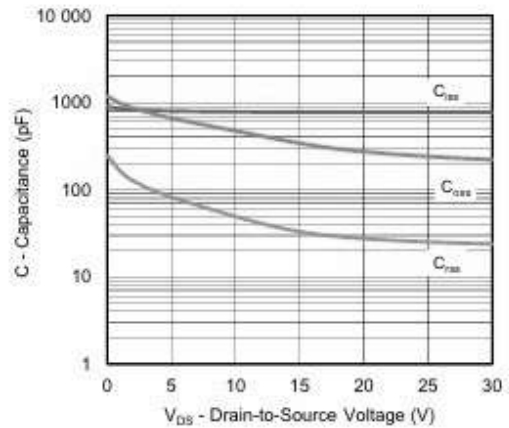
Output Characteristics



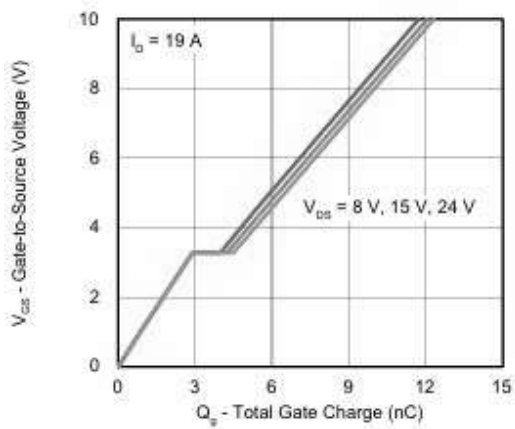
Transfer Characteristics



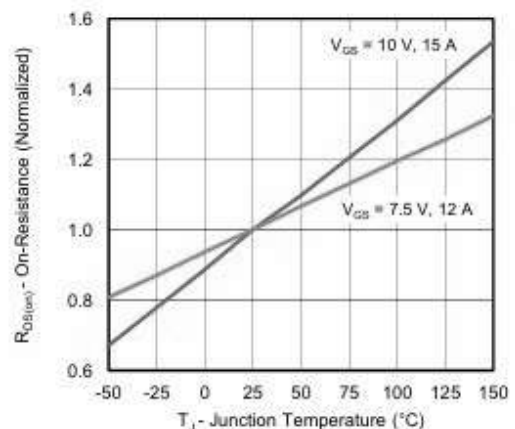
On-Resistance vs. Drain Current



Capacitance

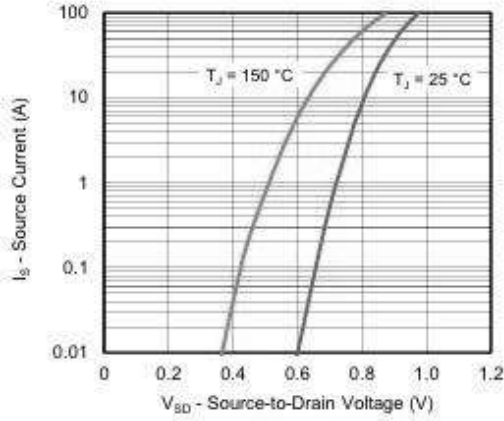


Gate Charge

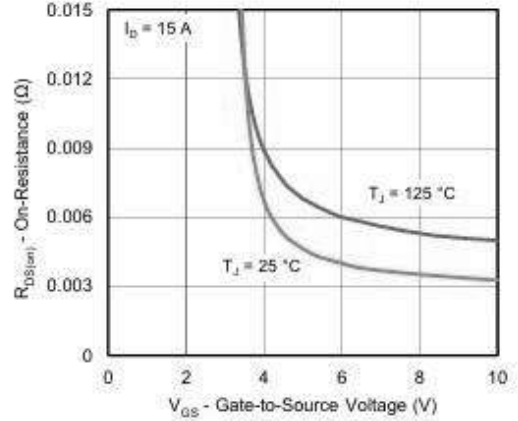


On-Resistance vs. Junction Temperature

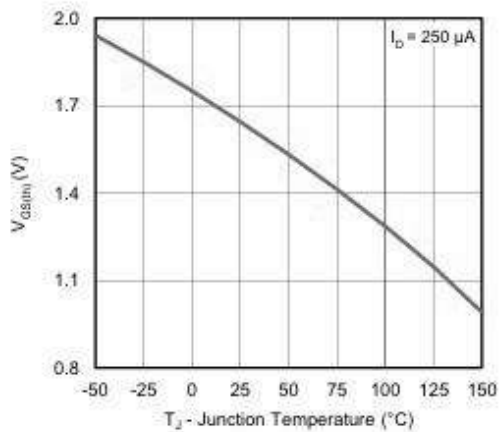
➤ Typical Characteristics



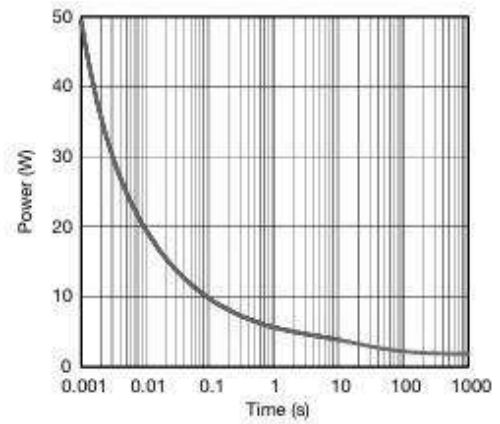
Source-Drain Diode Forward Voltage



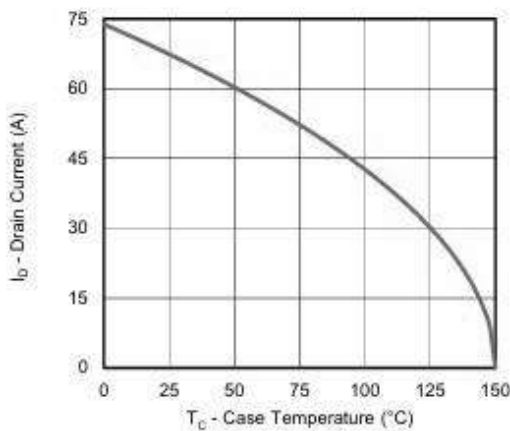
On-Resistance vs. Gate-to-Source Voltage



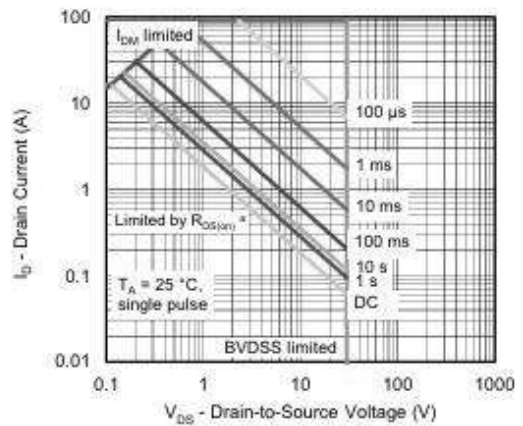
Threshold Voltage



Single Pulse Power, Junction-to-Ambient

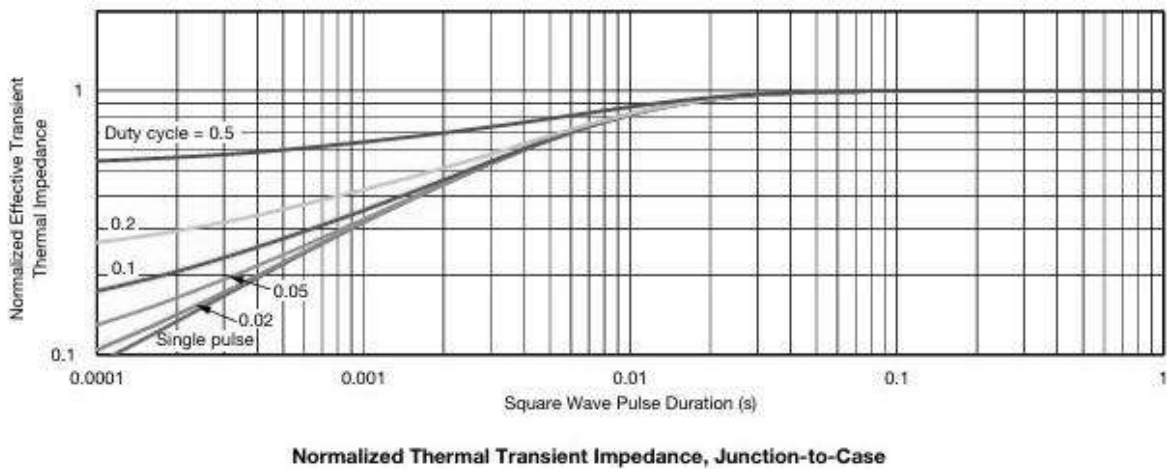
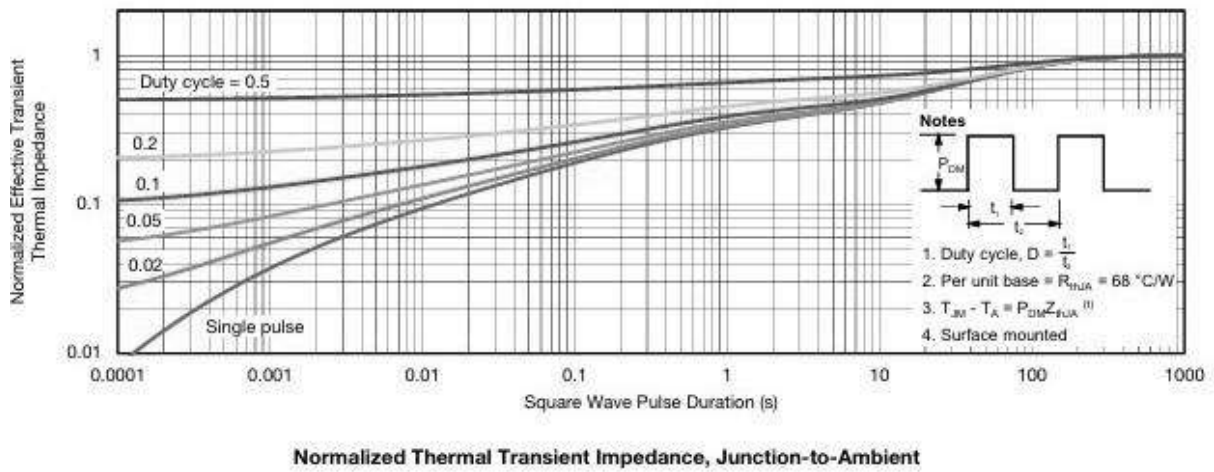
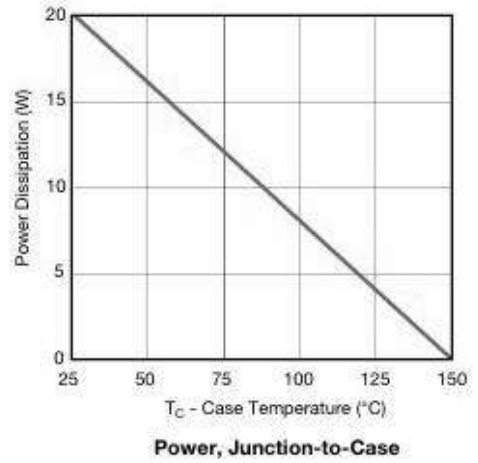
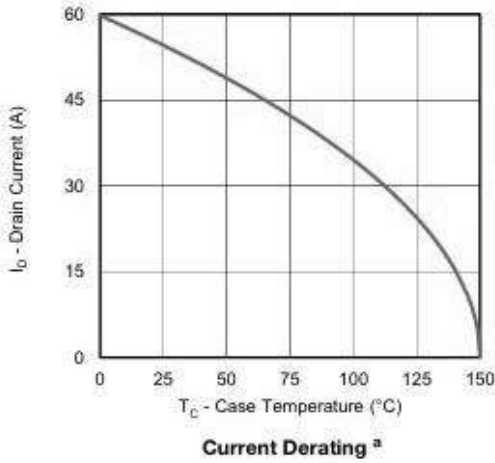


Current Derating ^a

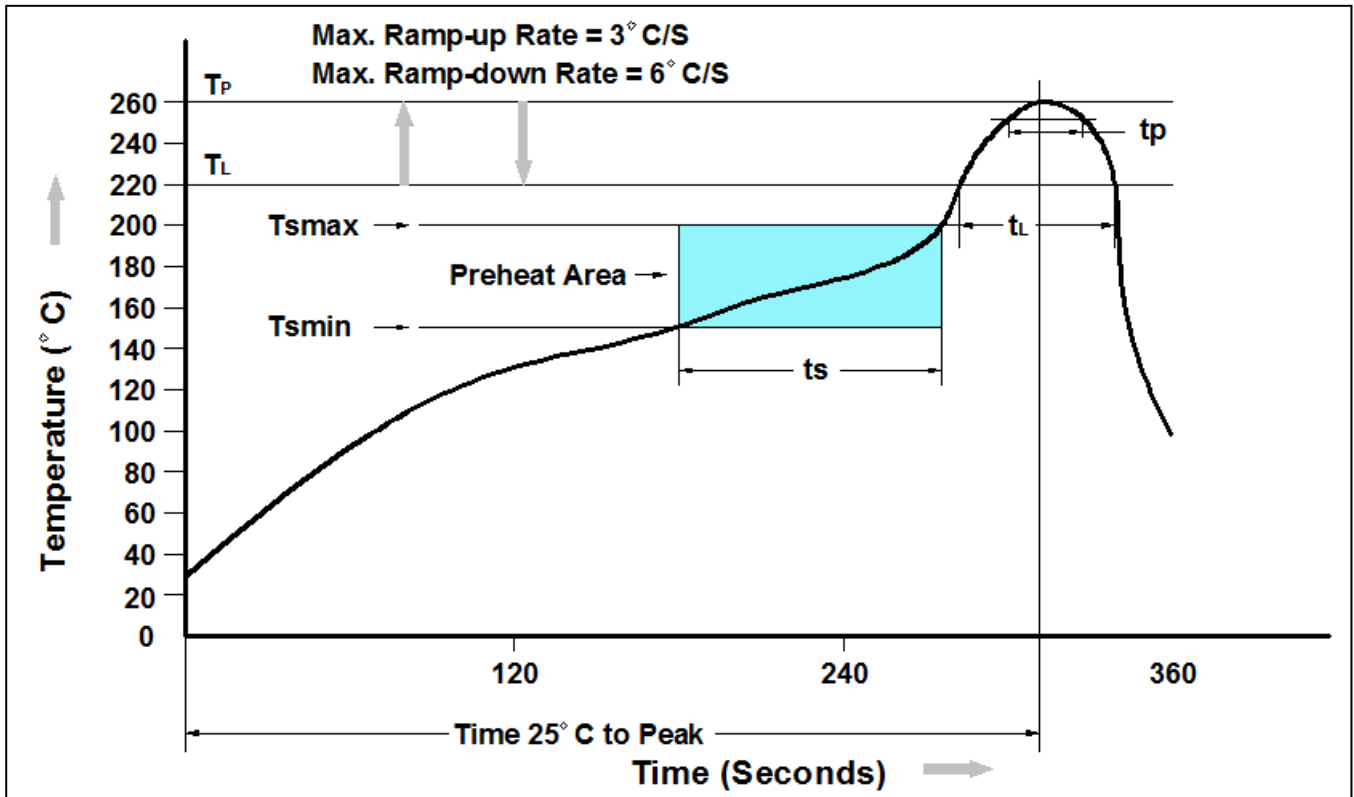


Safe Operating Area, Junction-to-Ambient

➤ Typical Characteristics



➤ Recommend IR Reflow Soldering Thermal Profile



Profile Feature	Pb-Free Assembly Profile
Temperature Min. (T _{smin})	150°C
Temperature Max. (T _{smax})	200°C
Time (t _s) from (T _{smin} to T _{smax})	60-120 seconds
Average Ramp-up Rate (t _L to t _P)	3°C/second max.
Liquidous Temperature (T _L)	217°C
Time (t _L) Maintained Above (T _L)	60 – 150 seconds
Peak Temperature	260°C +0°C / -5°C
Time (t _P) within 5°C of actual Peak Temperature	30 seconds
Ramp-down Rate (T _P to T _L)	6°C/second max
Time 25°C to Peak Temperature	8 minutes max.

➤ Ordering Information

Part Number	Description	Quantity
PAN75TY38CSA	DFN3.3x3.3-8L Reel	5000 pcs



PAN75TD38CSA

N-CH 30V Fast Switching MOSFET
 $V_{DS}=30V$, $I_D=65A$, $R_{DS(on)}=4.8m\Omega$

➤ Package Information (DFN3.3X3.3-8L)

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